# ROSi600

## Oxygen by Inert Gas Fusion Infrared Detection for Silicon Wafers

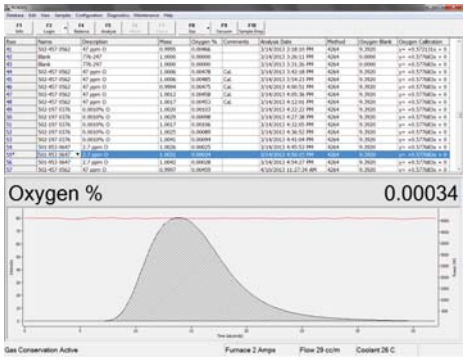

The ROSi600 was designed to meet the low-level sensitivity and high precision demands of the silicon industry. By combining the unmatched sensitivity of our solid-state infrared detection system with our novel sample loading system and programmable impulse furnace, the ROSi600 provides accurate and precise oxygen results in materials such as silicon wafers. The low-level sensitivity and high precision has also been applied to the metals industry, determining the oxygen content in high purity copper for electronics.

The loading head is designed for consistent sample loading, low atmospheric blank, and high carrier gas purity. Silicon wafers are consistently positioned in the furnace with the chute design of the loading head. Dual seals, a magnetic loading mechanism, and an integrated oxygen/moisture scrubber promote a near-zero atmospheric blank and maintain optimal carrier gas purity.

### Features

- Low-level, high-precision solid-state infrared (IR) detection
- Electrode Impulse Furnace with power or current control
- Accuracy and precision to low-ppm levels
- Low system blanks with wafer-friendly loading head
- Safety-protected reagent train
- Reduced maintenance with improved gas transfer
- Oxygen output in ppma
- Windows®-based operating system

***The zero blank loading head is designed for consistent wafer loading along with pins, chips, and powders.***




***System interface incorporates sample information, sample results, statistics, and system controls.***

Delivering the Right Results